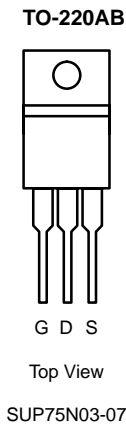




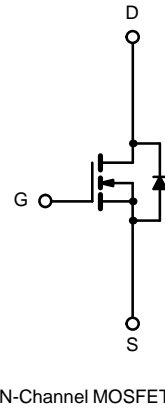
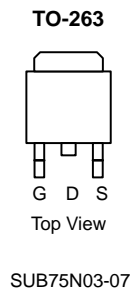
N-Channel 30-V (D-S) 175°C MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.007 @ $V_{GS} = 10$ V	75 ^a
	0.01 @ $V_{GS} = 4.5$ V	70

175°C Rated
Maximum Junction Temperature
TrenchFET®
Power MOSFETs



DRAIN connected to TAB



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	I_D	75 ^a	A
	$T_C = 100^\circ\text{C}$		64	
Pulsed Drain Current		I_{DM}	240	
Avalanche Current		I_{AR}	75	
Repetitive Avalanche Energy ^b		E_{AR}	280	mJ
Power Dissipation		P_D	120 ^c	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Limit	Unit
Junction-to-Ambient	PCB Mount (TO-263) ^d	R_{thJA}	40	$^\circ\text{C/W}$
	Free Air (TO-220AB)		62.5	
Junction-to-Case		R_{thJC}	1.25	

Notes:

- a. Package limited.
- b. Duty cycle $\leq 1\%$.
- c. See SOA curve for voltage derating.
- d. When mounted on 1" square PCB (FR-4 material).



MOSFET SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _{DS} = 250 μA	1	2		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 125°C			50	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 175°C			150	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		0.006	0.007	Ω
		V _{GS} = 10 V, I _D = 30 A, T _J = 125°C			0.011	
		V _{GS} = 10 V, I _D = 30 A, T _J = 175°C			0.015	
		V _{GS} = 4.5 V, I _D = 20 A			0.01	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	20			S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		5600		pF
Output Capacitance	C _{oss}			1100		
Reverse Transfer Capacitance	C _{rss}			450		
Total Gate Charge ^c	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 75 A		70	130	nC
Gate-Source Charge ^c	Q _{gs}			18		
Gate-Drain Charge ^c	Q _{gd}			10		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 15 V, R _L = 0.2 Ω I _D = 75 A, V _{GEN} = 10 V, R _G = 2.5 Ω		18	30	ns
Rise Time ^c	t _r			12	20	
Turn-Off Delay Time ^c	t _{d(off)}			60	120	
Fall Time ^c	t _f			22	40	
Source-Drain Diode Ratings and Characteristics (T_C = 25°C)^b						
Continuous Current	I _S				75	A
Pulsed Current	I _{SM}				200	
Forward Voltage ^a	V _{SD}	I _F = 75 A, V _{GS} = 0 V		1.2	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 75 A, di/dt = 100 A/μs		55	100	ns

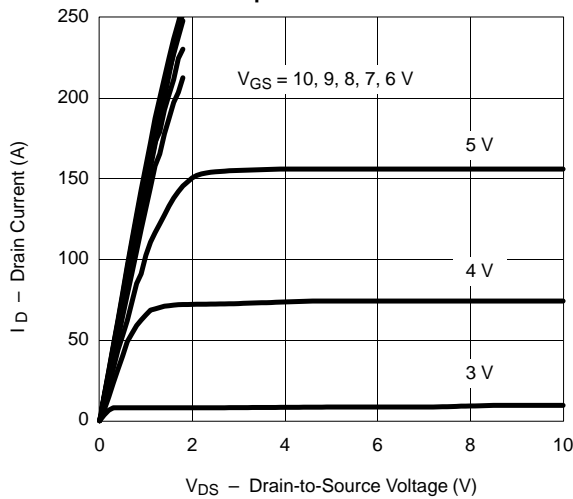
Notes:

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

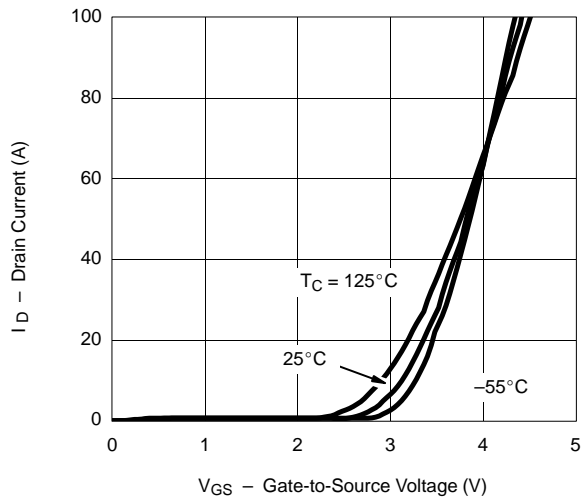


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

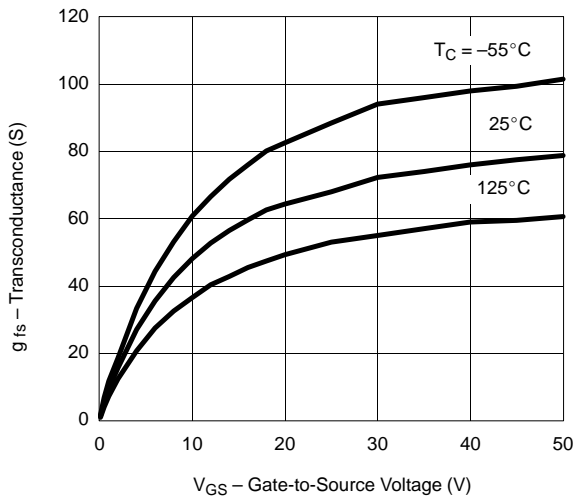
Output Characteristics



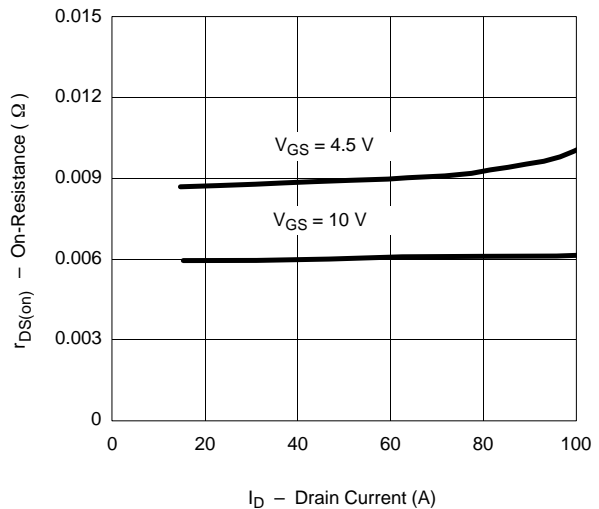
Transfer Characteristics



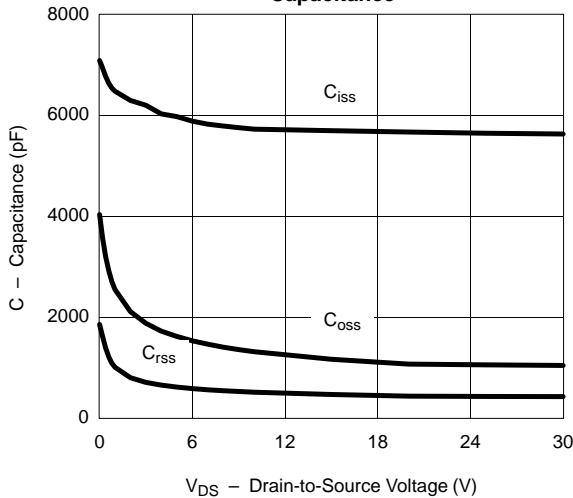
Transconductance



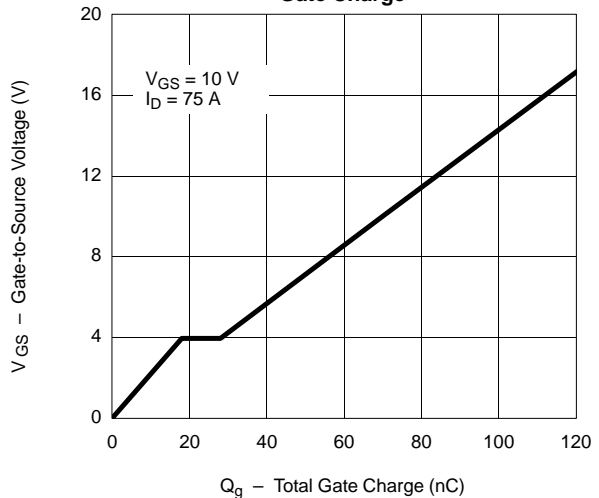
On-Resistance vs. Drain Current



Capacitance

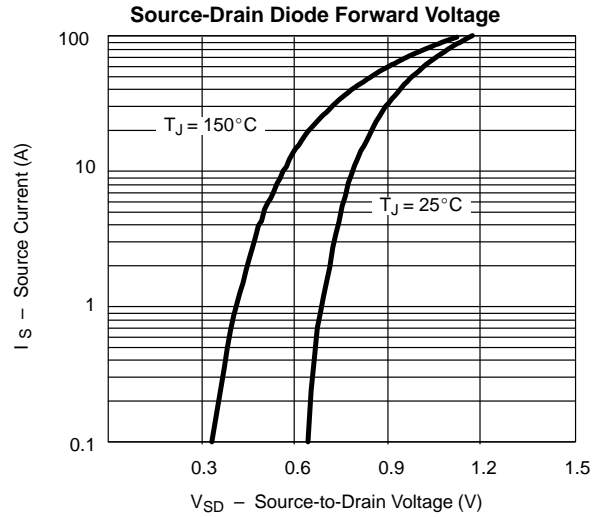
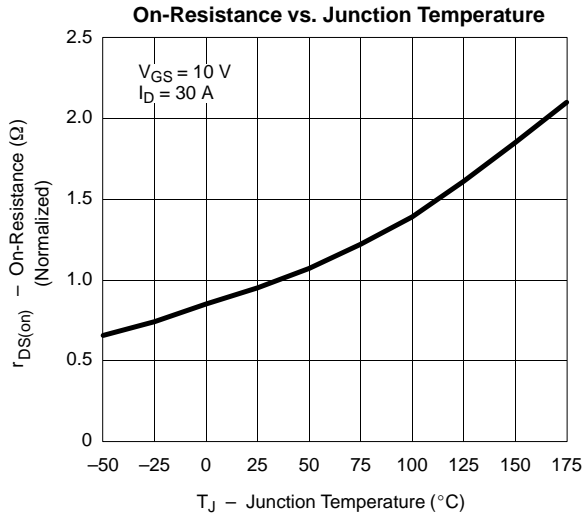


Gate Charge





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



THERMAL RATINGS

